

# High Power GaAs SPDT Switch DC - 2.0 GHz

### Features

- Positive Supply and Control Voltages
- 1 dB Compression Point: +36 dBm Typical, 8 V
- 3rd Order Intercept Point: +65 dBm Typical, 8 V
- Low Insertion Loss: 0.4 dB Typical
- Low Power Consumption: 100 μW
- Fast Switching Speed

## Description

M/A-COM's SW-277 is a GaAs MMIC SPDT switch in a SOIC-8 lead surface mount plastic package. The SW-277 is ideally suited for use where low power consumption is required.

Typical applications include transmit/receive switching, switch matrices and switched filter banks in systems such as radio and cellular equipment, PCM, GPS, fiber optic modules, and other battery powered radio equipment.

The SW-277 is fabricated using a monolithic GaAs MMIC using a mature 1 micron process. The process features full chip passivation for increased performance and reliability.

# Ordering Information<sup>1</sup>

Part Number	Package		
SW-277	Bulk Packaging		
SW-277TR	1000 piece reel		

1. Reference Application Note M513 for reel size information.

# Truth Table<sup>2</sup>

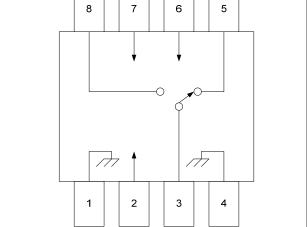
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Con Inp	itrol uts	Condition of Switch RF Common to Each RF P	
Α	В	RF1	RF2
1	0	Off	On
0	1	On	Off

"0" = 0 to +0.2 V @ 20 μA maximum.
 "1" = +5 V @ 20 μA typical to 10 V @ 500 μA maximum.

 Functional Schematic

 8
 7
 6
 9



## Pin Configuration

Pin No.	Description	Pin No.	Description
1	Ground, Thermal Contact	5	RF Port 1 <sup>3</sup>
2	V <sub>DD</sub>	6	Control A
3	RFC <sup>3</sup>	7	Control B
4	Ground, Thermal Contact	8	RF Port 2 <sup>3</sup>

3. External DC blocking capacitors required on all RF ports.

## Absolute Maximum Ratings <sup>4,5</sup>

Parameter	Absolute Maximum		
Input Power - 0.5 - 2.0 GHz 5 V Control and Supply 8 V Control and Supply 10 V Control and Supply	+37 dBm +40 dBm +42 dBm		
Power Dissipation	1.0 W		
Supply Voltage	$-1 \text{ V} \leq \text{V}_{\text{DD}} \leq + 12 \text{ V}$		
Control Voltage	$-1 \text{ V} \le \text{V}_{\text{C}} \le \text{V}_{\text{DD}} + 0.2 \text{ V}$		
Operating Temperature	-40°C to +85°C		
Storage Temperature	-65°C to +150°C		
Thermal Resistance <sup>6</sup>	θjc = 87°C/W		

4. Exceeding any one or combination of these limits may cause permanent damage to this device.

M/A-COM does not recommend sustained operation near these survivability limits.

 Thermal resistance is given for T<sub>A</sub> = 25°C. T<sub>CASE</sub> is the temperature of leads 1 and 4.

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and/or prototype measurements. Commitment to develop is not guaranteed. **PRELIMINARY:** Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. *MM* 

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Rev. V6



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Rev. V6

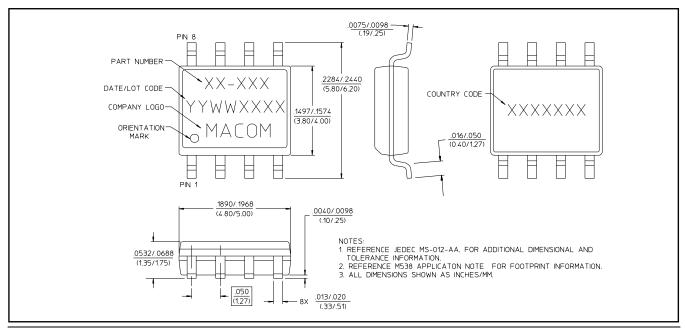
# Electrical Specifications <sup>7</sup>: $T_A = +25$ °C, $V_{DD} = +5$ V, $V_C = +5$ V / 0 V, $P_{IN} = +30$ dBm

Parameter	Test Conditions	Units	Min.	Typ. <sup>8</sup>	Max.
Insertion Loss	DC - 0.5 GHz 0.5 - 1.0 GHz 1.0 - 2.0 GHz	dB dB dB		0.45 0.55 0.6	 0.65 
Isolation	DC - 0.5 GHz 0.5 - 1.0 GHz 1.0 - 2.0 GHz	dB dB dB	 27 	30 32 27	
VSWR	DC - 2.0 GHz	Ratio	_	1.2:1	_
1 dB Compression	Input Power (5 V Supply/Control) 0.9 GHz Input Power (8 V Supply/Control) 0.9 GHz	dBm dBm	_	33 35.8	_
Trise, Tfall	10% to 90% RF, 90% to 10% RF	nS	—	30	_
Ton, Toff	50% Control to 90% RF, 50% Control to 10% RF	nS	—	35	_
Transients	In-Band	mV	_	12	_
3rd Order Intercept	Measured Relative to Input Power, two-tone up to +10 dBm (5 V Supply/Control) 0.9 GHz (8 V Supply/Control) 0.9 GHz	dBm dBm	_	55 65	
Control Current	V <sub>C</sub> = +5 V	μA	—	—	20
Supply Current	V <sub>DD</sub> = +5 V	μA	—	—	60

7. All specifications apply when operated with control voltages of 0 V for V<sub>C</sub> low and 5 to 10 V for V<sub>C</sub> high, and 50 Ω impedance at all RF ports, unless otherwise specified. High power (greater than 1 W) handling specifications apply to cold switching only. For input powers under 1 W, hot switching can be used. The high control voltage must be within ± 0.2 V of the supply voltage. External DC blocking capacitors are required on all RF ports.

8. Typical values listed for middle of frequency range noted.

# SOIC-8



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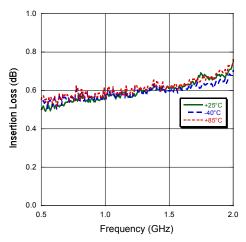


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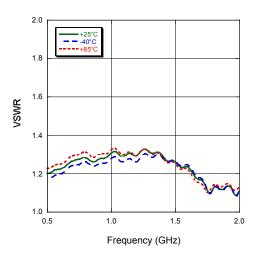
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# **Typical Performance Curves**

#### Insertion Loss



#### VSWR



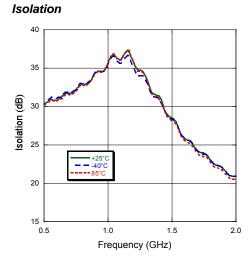
#### **Handling Procedures**

Please observe the following precautions to avoid damage:

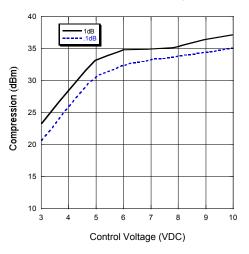
## **Static Sensitivity**

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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Compression vs. Control Voltage @ 900 MHz



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<sup>3</sup>